

# n-Channel Power MOSFET

OptiMOS™  
BSC024NE2LS

## Data Sheet

2.1, 2011-09-20  
Final

Industrial & Multimarket

## 1 Description

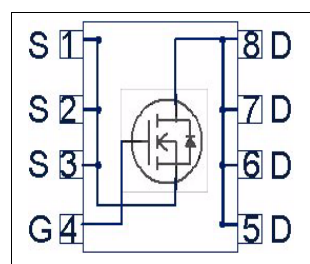
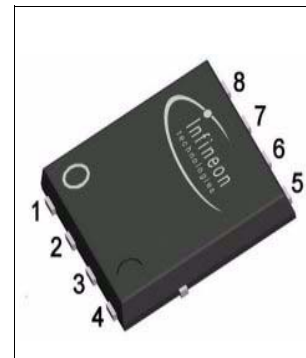
OptiMOS™25V products are class leading power MOSFETs for highest power density and energy efficient solutions. Ultra low gate- and output charges together with lowest on state resistance in small footprint packages make OptiMOS™ 25V the best choice for the demanding requirements of voltage regulator solutions in Servers, Datacom and Telecom applications. Super fast switching Control FETs together with low EMI Sync FETs provide solutions that are easy to design in. OptiMOS™ products are available in high performance packages to tackle your most challenging applications giving full flexibility in optimizing space, efficiency and cost. OptiMOS™ products are designed to meet and exceed the energy efficiency and power density requirements of the sharpened next generation voltage regulation standards in computing applications.

### Features

- Optimized for high performance buck converters
- 100% avalanche tested
- Very low on-resistance  $R_{DS(on)}$  @  $V_{GS}=4.5\text{ V}$
- N-channel
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Superior thermal resistance
- Pb-free plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

### Applications

- On board power for server
- Power management for high performance computing
- Synchronous rectification
- High power density point of load converters



**Table 1 Key Performance Parameters**

| Parameter        | Value | Unit | Related Links                                                                                                                                                    |
|------------------|-------|------|------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| $V_{DS}$         | 25    | V    | <a href="#">IFX OptiMOS webpage</a><br><a href="#">IFX OptiMOS product brief</a><br><a href="#">IFX OptiMOS spice models</a><br><a href="#">IFX Design tools</a> |
| $R_{DS(on),max}$ | 2.4   | mΩ   |                                                                                                                                                                  |
| $I_D$            | 100   | A    |                                                                                                                                                                  |
| $Q_{OSS}$        | 13    | nC   |                                                                                                                                                                  |
| $Q_{g,typ}$      | 23    |      |                                                                                                                                                                  |

| Type        | Package    | Marking  |
|-------------|------------|----------|
| BSC024NE2LS | PG-TDSON-8 | 024NE2LS |

1) J-STD20 and JESD22

## 2 Maximum ratings

at  $T_j = 25\text{ °C}$ , unless otherwise specified.

**Table 2 Maximum ratings**

| Parameter                                     | Symbol         | Values    |      |      | Unit | Note / Test Condition                                                     |
|-----------------------------------------------|----------------|-----------|------|------|------|---------------------------------------------------------------------------|
|                                               |                | Min.      | Typ. | Max. |      |                                                                           |
| Continuous drain current                      | $I_D$          | -         | -    | 100  | A    | $V_{GS}=10\text{ V}$ , $T_C=25\text{ °C}$                                 |
|                                               |                | -         | -    | 70   |      | $V_{GS}=10\text{ V}$ , $T_C=100\text{ °C}$                                |
|                                               |                | -         | -    | 93   |      | $V_{GS}=4.5\text{ V}$ , $T_C=25\text{ °C}$                                |
|                                               |                | -         | -    | 59   |      | $V_{GS}=4.5\text{ V}$ , $T_C=100\text{ °C}$                               |
|                                               |                | -         | -    | 25   |      | $V_{GS}=10\text{ V}$ , $T_A=25\text{ °C}$ , $R_{thJA}=50\text{ K/W}^{1)}$ |
| Pulsed drain current <sup>2)</sup>            | $I_{D,pulse}$  | -         | -    | 400  |      | $T_C=25\text{ °C}$                                                        |
| Avalanche current, single pulse <sup>3)</sup> | $I_{AS}$       | -         | -    | 50   |      |                                                                           |
| Avalanche energy, single pulse                | $E_{AS}$       | -         | -    | 40   | mJ   | $I_D=40\text{ A}$ , $R_{GS}=25\text{ }\Omega$                             |
| Gate source voltage                           | $V_{GS}$       | -20       | -    | 20   | V    |                                                                           |
| Power dissipation                             | $P_{tot}$      | -         | -    | 48   | W    | $T_C=25\text{ °C}$                                                        |
|                                               |                | -         | -    | 2.5  |      | $T_A=25\text{ °C}$ , $R_{thJA}=50\text{ K/W}^{1)}$                        |
| Operating and storage temperature             | $T_j, T_{stg}$ | -55       | -    | 150  | °C   |                                                                           |
| IEC climatic category; DIN IEC 68-1           |                | 55/150/56 |      |      |      |                                                                           |

1) Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

2) See figure 3 for more detailed information

3) See figure 13 for more detailed information

## 3 Thermal characteristics

**Table 3 Thermal characteristics**

| Parameter                           | Symbol     | Values |      |      | Unit | Note / Test Condition                        |
|-------------------------------------|------------|--------|------|------|------|----------------------------------------------|
|                                     |            | Min.   | Typ. | Max. |      |                                              |
| Thermal resistance, junction - case | $R_{thJC}$ | -      | -    | 2.6  | K/W  |                                              |
|                                     |            | -      | -    | 20   |      | top                                          |
| Device on PCB                       | $R_{thJA}$ | -      | -    | 50   |      | 6 cm <sup>2</sup> cooling area <sup>1)</sup> |

1) Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air

## 4 Electrical characteristics

Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified.

**Table 4 Static characteristics**

| Parameter                        | Symbol        | Values |      |      | Unit             | Note / Test Condition                                               |
|----------------------------------|---------------|--------|------|------|------------------|---------------------------------------------------------------------|
|                                  |               | Min.   | Typ. | Max. |                  |                                                                     |
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | 25     | -    | -    | V                | $V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$                             |
| Gate threshold voltage           | $V_{GS(th)}$  | 1.2    | -    | 2    |                  | $V_{DS}=V_{GS}$ , $I_D=250\text{ }\mu\text{A}$                      |
| Zero gate voltage drain current  | $I_{DSS}$     | -      | 0.1  | 1    | $\mu\text{A}$    | $V_{DS}=25\text{ V}$ , $V_{GS}=0\text{ V}$ ,<br>$T_j=25\text{ °C}$  |
|                                  |               | -      | 10   | 100  |                  | $V_{DS}=25\text{ V}$ , $V_{GS}=0\text{ V}$ ,<br>$T_j=125\text{ °C}$ |
| Gate-source leakage current      | $I_{GSS}$     | -      | 10   | 100  | nA               | $V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$                          |
| Drain-source on-state resistance | $R_{DS(on)}$  | -      | 2.7  | 3.4  | $\text{m}\Omega$ | $V_{GS}=4.5\text{ V}$ , $I_D=30\text{ A}$ ,                         |
|                                  |               | -      | 2    | 2.4  |                  | $V_{GS}=10\text{ V}$ , $I_D=30\text{ A}$ ,                          |
| Gate resistance                  | $R_G$         | -      | 0.9  | -    | $\Omega$         |                                                                     |
| Transconductance                 | $g_{fs}$      | 55     | 110  | -    | S                | $ V_{DS}  > 2 I_D R_{DS(on)max}$ ,<br>$I_D=30\text{ A}$             |

**Table 5 Dynamic characteristics**

| Parameter                    | Symbol       | Values |      |      | Unit | Note / Test Condition                                                                        |
|------------------------------|--------------|--------|------|------|------|----------------------------------------------------------------------------------------------|
|                              |              | Min.   | Typ. | Max. |      |                                                                                              |
| Input capacitance            | $C_{iss}$    | -      | 1700 | -    | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=12\text{ V}$ ,<br>$f=1\text{ MHz}$                             |
| Output capacitance           | $C_{oss}$    | -      | 650  | -    |      |                                                                                              |
| Reverse transfer capacitance | $C_{rss}$    | -      | 71   | -    |      |                                                                                              |
| Turn-on delay time           | $t_{d(on)}$  | -      | 4.1  | -    | ns   | $V_{DD}=12\text{ V}$ , $V_{GS}=10\text{ V}$ ,<br>$I_D=30\text{ A}$ , $R_G=1.6\text{ }\Omega$ |
| Rise time                    | $t_r$        | -      | 3.6  | -    |      |                                                                                              |
| Turn-off delay time          | $t_{d(off)}$ | -      | 19   | -    |      |                                                                                              |
| Fall time                    | $t_f$        | -      | 2.6  | -    |      |                                                                                              |

**Electrical characteristics**
**Table 6 Gate charge characteristics<sup>1)</sup>**

| Parameter                    | Symbol        | Values |      |      | Unit | Note / Test Condition                                                              |
|------------------------------|---------------|--------|------|------|------|------------------------------------------------------------------------------------|
|                              |               | Min.   | Typ. | Max. |      |                                                                                    |
| Gate to source charge        | $Q_{gs}$      | -      | 4.4  | -    | nC   | $V_{DD}=12\text{ V}$ ,<br>$I_D=30\text{ A}$ ,<br>$V_{GS}=0\text{ to }4.5\text{ V}$ |
| Gate charge at threshold     | $Q_{g(th)}$   | -      | 2.7  | -    |      |                                                                                    |
| Gate to drain charge         | $Q_{gd}$      | -      | 2.6  | -    |      |                                                                                    |
| Switching charge             | $Q_{sw}$      | -      | 4.3  | -    |      |                                                                                    |
| Gate charge total            | $Q_g$         | -      | 11   | -    |      |                                                                                    |
| Gate plateau voltage         | $V_{plateau}$ | -      | 2.6  | -    | V    |                                                                                    |
| Gate charge total            | $Q_g$         | -      | 23   | -    | nC   | $V_{DD}=12\text{ V}$ ,<br>$I_D=30\text{ A}$ ,<br>$V_{GS}=0\text{ to }10\text{ V}$  |
| Gate charge total, sync. FET | $Q_{g(sync)}$ | -      | 10   | -    |      | $V_{DS}=0.1\text{ V}$ ,<br>$V_{GS}=0\text{ to }4.5\text{ V}$                       |
| Output charge                | $Q_{oss}$     | -      | 13   | -    |      | $V_{DD}=12\text{ V}$ , $V_{GS}=0\text{ V}$                                         |

1) See figure 16 for gate charge parameter definition

**Table 7 Reverse diode characteristics**

| Parameter                        | Symbol        | Values |      |      | Unit | Note / Test Condition                                                 |
|----------------------------------|---------------|--------|------|------|------|-----------------------------------------------------------------------|
|                                  |               | Min.   | Typ. | Max. |      |                                                                       |
| Diode continuous forward current | $I_s$         | -      | -    | 48   | A    | $T_C=25\text{ °C}$                                                    |
| Diode pulse current              | $I_{s,pulse}$ | -      | -    | 192  |      |                                                                       |
| Diode forward voltage            | $V_{SD}$      | -      | 0.85 | 1    | V    | $V_{GS}=0\text{ V}$ , $I_F=30\text{ A}$ ,<br>$T_j=25\text{ °C}$       |
| Reverse recovery charge          | $Q_{rr}$      | -      | 15   | -    | nC   | $V_R=15\text{ V}$ , $I_F=I_s$ ,<br>$dI_F/dt=400\text{ A}/\mu\text{s}$ |

## 5 Electrical characteristics diagrams

Table 8

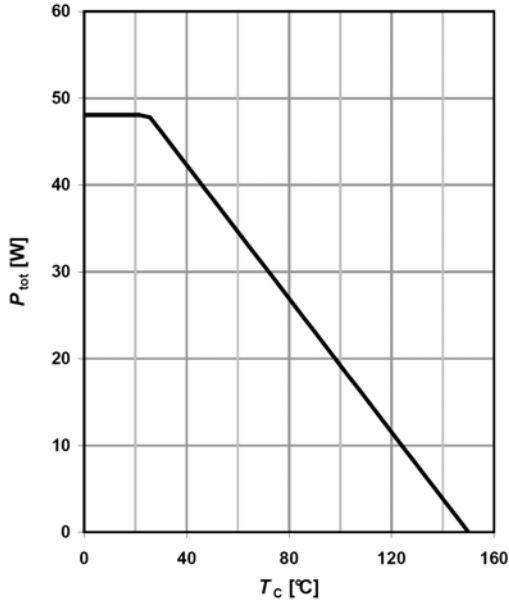
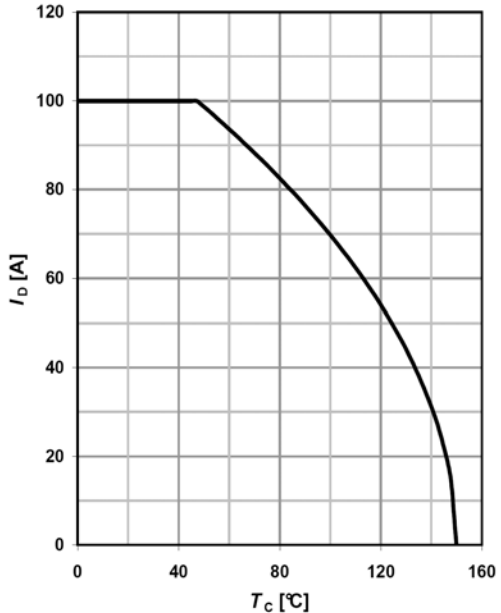
| 1 Power dissipation                                                                                                            | 2 Drain current                                                                                                                                      |
|--------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------|
|  <p><math>P_{\text{tot}} = f(T_c)</math></p> |  <p><math>I_D = f(T_c)</math>; parameter: <math>V_{GS}</math></p> |

Table 9

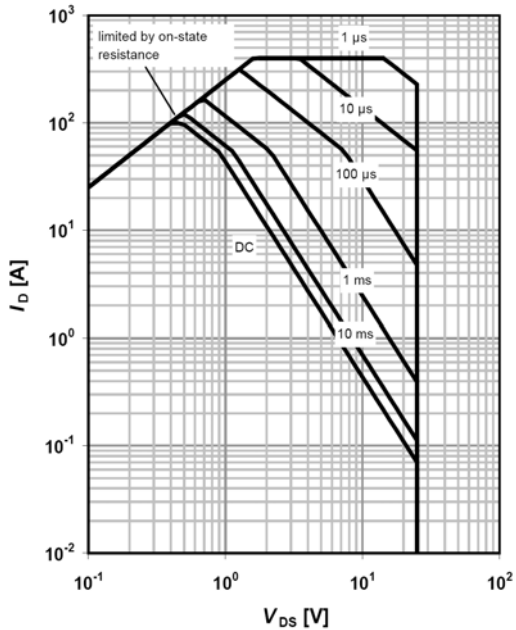
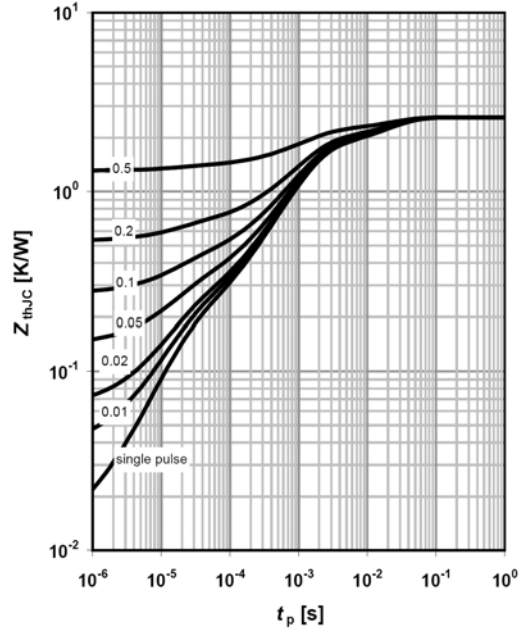
| 3 Safe operating area $T_c = 25^\circ\text{C}$                                                                                                                                                                | 4 Max. transient thermal impedance                                                                                                                                |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------|
|  <p><math>I_D = f(V_{DS})</math>; <math>T_J = 25^\circ\text{C}</math>; <math>D = 0</math>; parameter: <math>T_p</math></p> |  <p><math>Z_{(thJC)} = f(t_p)</math>; parameter: <math>D = t_p / T</math></p> |



Table 10

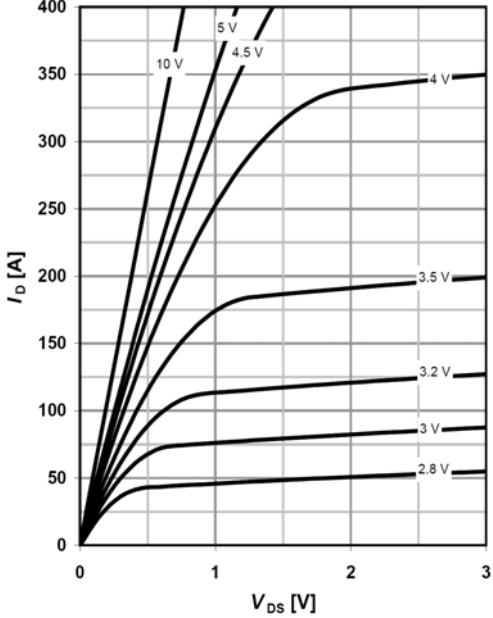
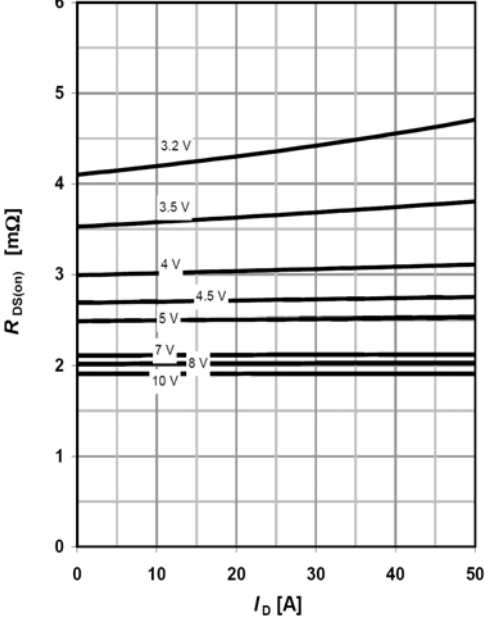
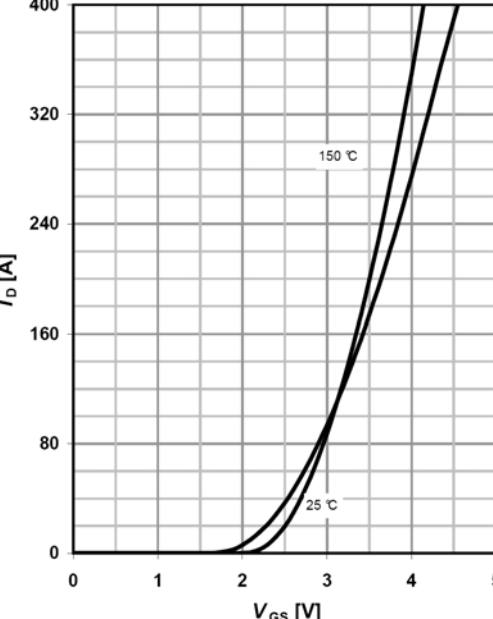
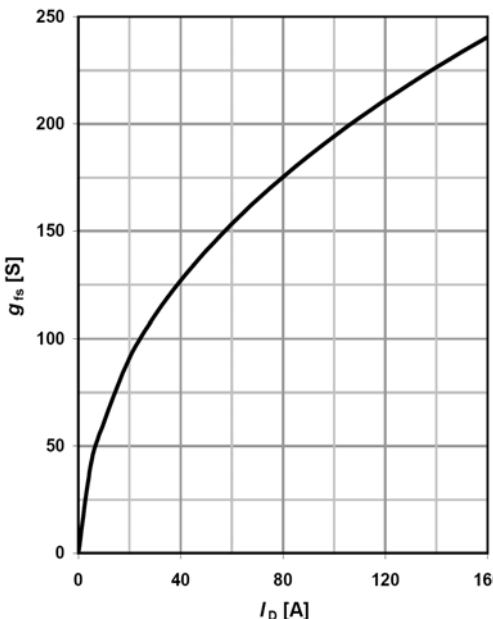
| 5 Typ. output characteristics $T_c=25\text{ °C}$                                                                                                                      | 6 Typ. drain-source on-state resistance                                                                                                                                    |
|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
|  <p><math>I_D = f(V_{DS}); T_j = 25\text{ °C}; \text{parameter: } V_{GS}</math></p> |  <p><math>R_{DS(on)} = f(I_D); T_j = 25\text{ °C}; \text{parameter: } V_{GS}</math></p> |

Table 11

| 7 Typ. transfer characteristics                                                                                                                            | 8 Typ. forward transconductance                                                                                                              |
|------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------|
|  <p><math>I_D = f(V_{GS});  V_{DS}  &gt; 2 I_D R_{DS(on)max}</math></p> |  <p><math>g_{fs} = f(I_D); T_j = 25\text{ °C}</math></p> |

Electrical characteristics diagrams

Table 12

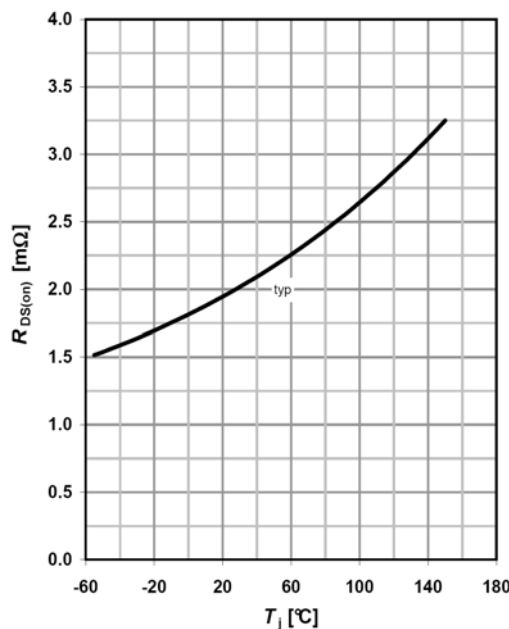
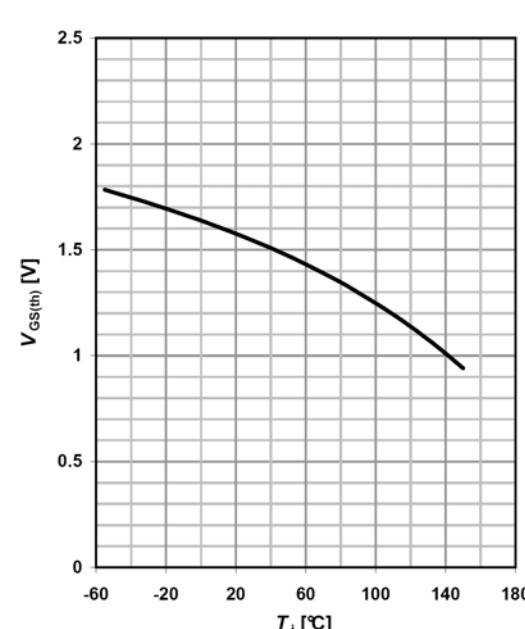
| 9 Drain-source on-state resistance                                                 | 10 Typ. gate threshold voltage                                                      |
|------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
|  |  |
| $R_{DS(on)}=f(T_j)$ ; $I_D=30\text{ A}$ ; $V_{GS}=10\text{ V}$                     | $V_{GS(th)}=f(T_j)$ ; $V_{GS}=V_{DS}$ ; $I_D=250\text{ }\mu\text{A}$                |

Table 13

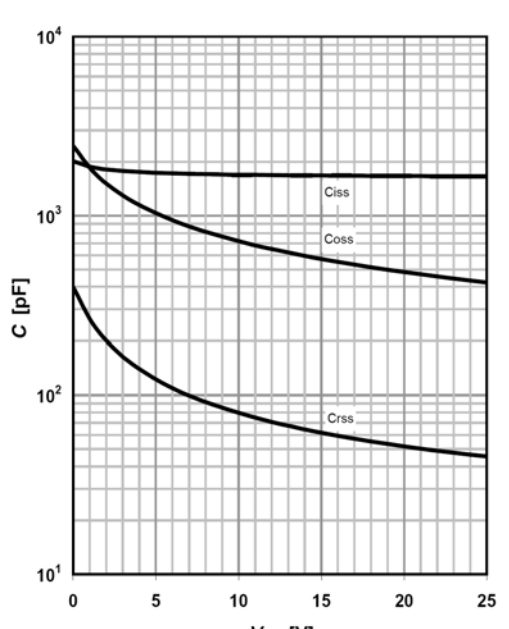
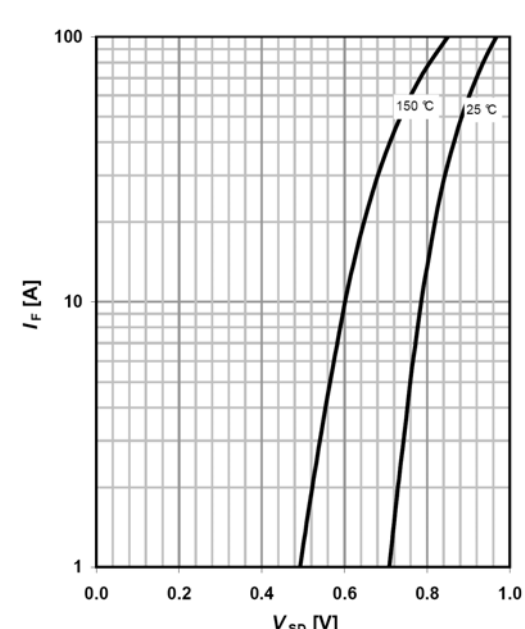
| 11 Typ. capacitances                                                                | 12 Forward characteristics of reverse diode                                          |
|-------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------|
|  |  |
| $C=f(V_{DS})$ ; $V_{GS}=0\text{ V}$ ; $f=1\text{ MHz}$                              | $I_F=f(V_{SD})$ ; parameter: $T_j$                                                   |



Table 14

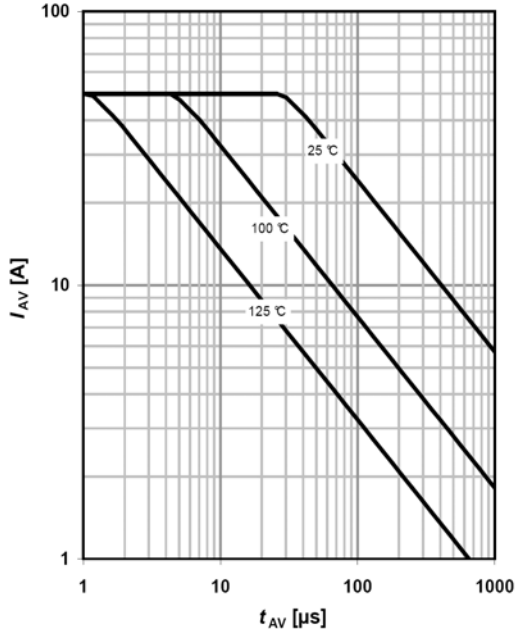
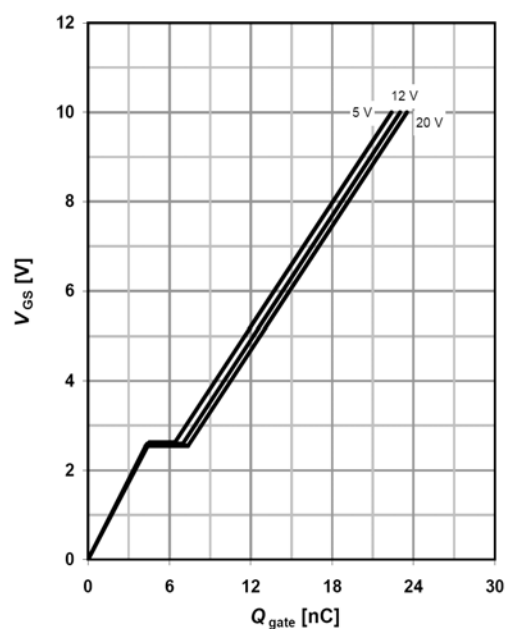
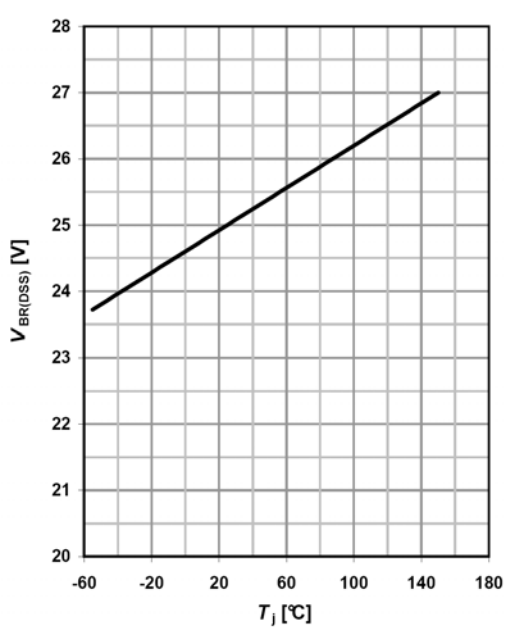
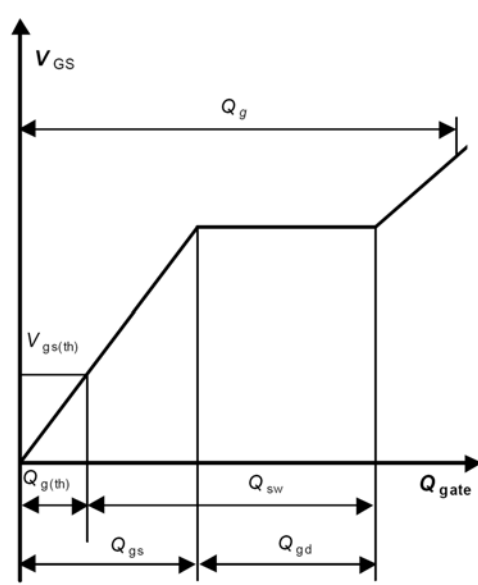
| 13 Avalanche characteristics                                                                                                                                                                  | 14 Typ. gate charge                                                                                                                                                                             |
|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
|  <p><math>I_{AS}=f(t_{AV})</math>; <math>R_{GS}=25\ \Omega</math>; parameter: <math>T_{j(start)}</math></p> |  <p><math>V_{GS}=f(Q_{gate})</math>; <math>I_D=30\text{ A}</math> pulsed; parameter: <math>V_{DD}</math></p> |

Table 15

| 15 Drain-source breakdown voltage                                                                                                                        | 16 Gate charge waveforms                                                             |
|----------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------|
|  <p><math>V_{BR(DSS)}=f(T_J)</math>; <math>I_D=1\text{ mA}</math></p> |  |

## 6 Package outline

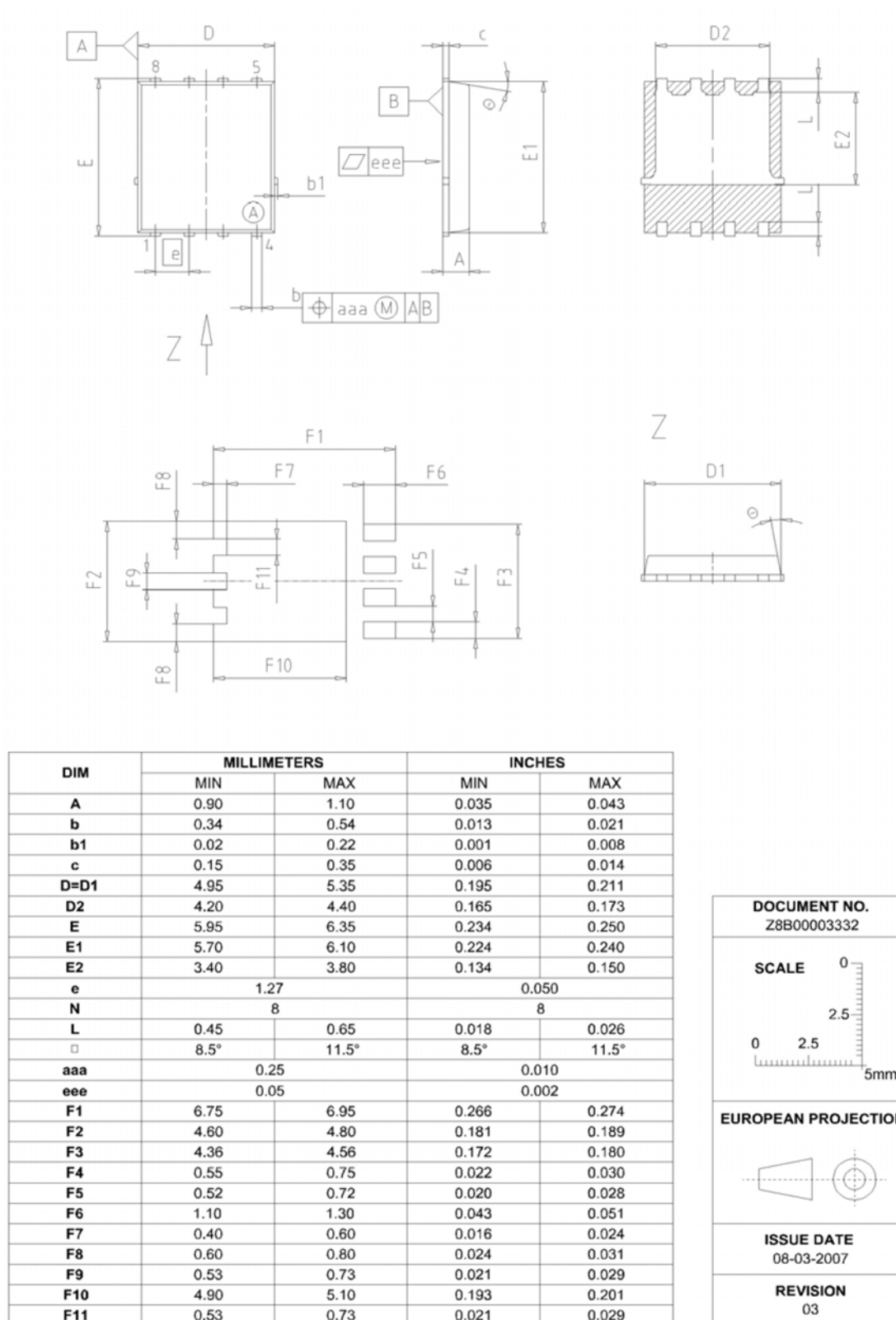
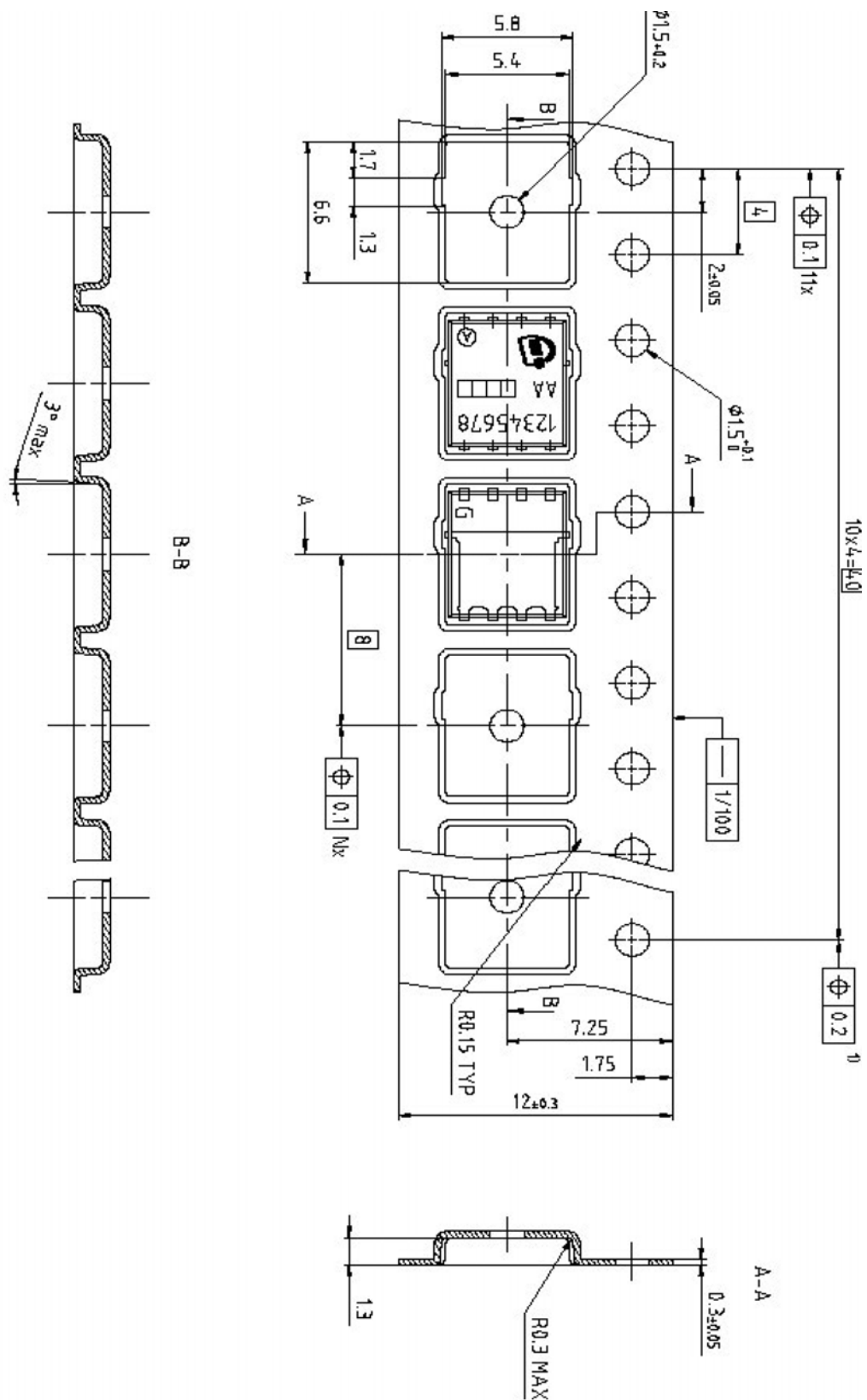


Figure 1 Outlines PG-TDSON-8, dimensions in mm/inches



**Figure 2** Outlines PG-TDSON-8 tape, dimension in mm/inches

## 7 Revision History

### Revision History: 2011-09-20, 2.1

#### Previous Revision:

| Revision | Subjects (major changes since last revision) |
|----------|----------------------------------------------|
| 0.2      | Release of Target data sheet                 |
| 1.0      | Release of Preliminary Data Sheet            |
| 2.0      | Release of Final data sheet                  |
| 2.1      | Update VGS(th)                               |

### We Listen to Your Comments

Any information within this document that you feel is wrong, unclear or missing at all?

Your feedback will help us to continuously improve the quality of this document.

Please send your proposal (including a reference to this document) to: [erratum@infineon.com](mailto:erratum@infineon.com)



Edition 2011-09-20

Published by

Infineon Technologies AG

81726 Munich, Germany

© 2011 Infineon Technologies AG

All Rights Reserved.

### Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

### Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office ([www.infineon.com](http://www.infineon.com)).

### Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

# Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[Infineon:](#)

[BSC024NE2LS](#) [BSC024NE2LSATMA1](#) [BSC024NE2LSXT](#)